

SMALL SIGNAL SCHOTTKY DIODES

VOLTAGE RANGE: 20 V

P_{tot}: 430 mW

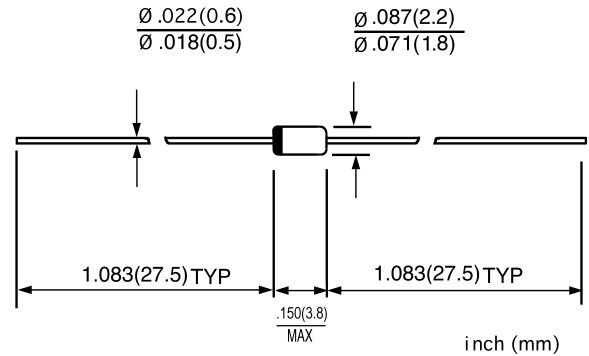
FEATURES

- ◇ Metal-to-silicon junction
- ◇ High breakdown voltage
- ◇ Low turn-on voltage
- ◇ Ultrafast switching speed
- ◇ Primarily intended for high level UHF/MHF detection and pulse applications with broad dynamic range

MECHANICAL DATA

- ◇ Case: JEDEC DO-35, glass case
- ◇ Polarity: Color band denotes cathode end
- ◇ Weight: Approx. 0.13 gram

DO - 35(GLASS)



ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	UNITS
Peak reverse voltage	V_{RRM}	20.0	V
Power dissipation (Infinite Heat Sink)	P_{tot}	430.0	mW
Forward continuous current	I_{FSM}	35.0	mA
Junction and storage temperature range	T_J/T_{STG}	-55 --- + 150	°C
Maximum lead temperature for soldering during 10S at 4mm from case	T_L	230	°C

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	UNITS
Reverse breakdown voltage @ $I_R=10 \mu A$	V_R	20.0			V
Leakage current @ $V_R=16V$	I_R			150	nA
Forward voltage drop @ $I_F=1mA$	V_F			0.41	V
Test pulse: $t_p \leq 300 \mu s$ $\delta < 2\%$ $I_F=35mA$	V_F			1.0	V
Junction capacitance @ $V_R=0V, f=1MHz$	C_J			2	pF
Thermal resistance	R_{JA}			400	K/W

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FIG.1 – TYPICAL CURRENT VERSUS FORWARD VOLTAGE AT DIFFERENT TEMPERATURES (TYPICAL VALUES)

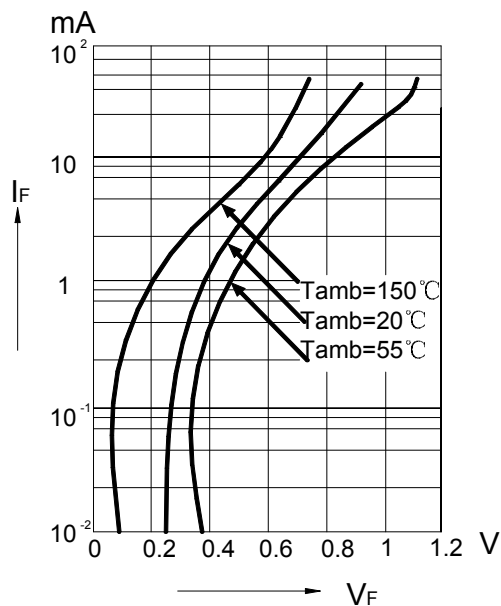


FIG.2 –FORWARD CURRENT VERSUS FORWARD VOLTAGE (TYPICAL VALUES)

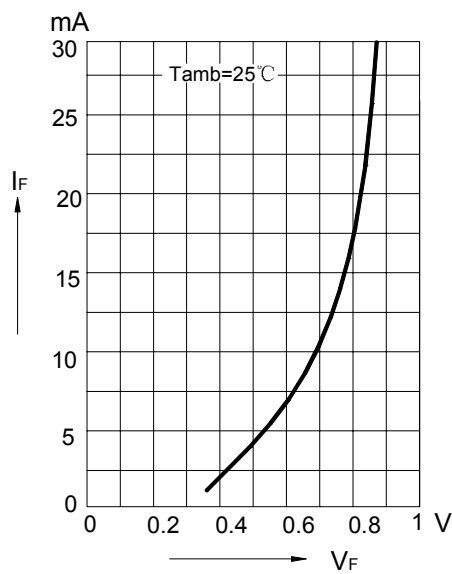


FIG.3 –REVERSE CURRENT VERSUS AMBIENT TEMPERATURE

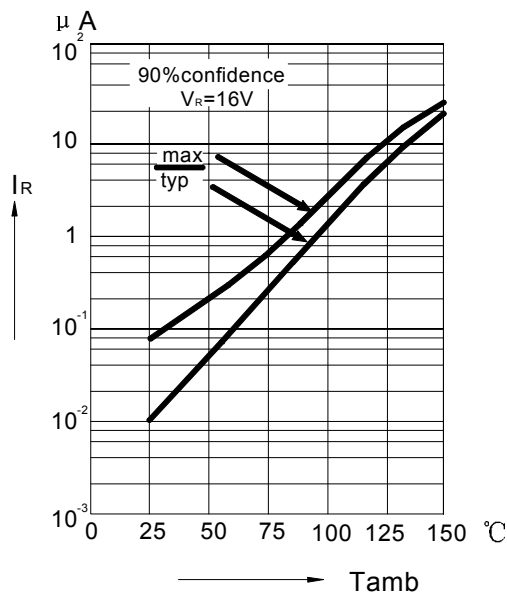


FIG.4 – REVERSE CURRENT VERSUS CONTINUOUS REVERSE VOLTAGE (TYPICAL VALUES)

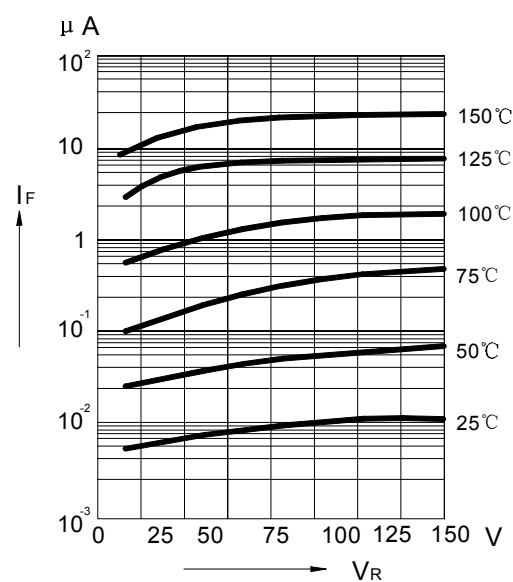


FIG.5 – CAPACITANCE CVERSUS REVERS APPLIED VOLTAGE VR (TYPICAL VALUES)

